

10 | 665, 645

EAST History

12/27/04

5:10 PM

BRS	6798	monolithic adj integrated adj circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	161	S31 and (schottky adj diodes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
IS&R	121364	((("326") or ("327"))).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	44	S32 and S33	USPAT
BRS	4309	(schottky adj diodes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	708	S33 and S35	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	4	S36 and (P-type adj well)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	799	(P-type adj well) and (n-type adj region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	889	istl	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	892	S39 or S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	176	micrel-inc.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
IS&R	121364	((("326") or ("327"))).CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	892	istl or (integrated adj schottky adj transistor adj logic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
BRS	3	(integrated adj schottky adj transistor adj logic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB